



JST236W-800D

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	- -	MAX.	5	mA
				10	
V _{GT}		ALL	MAX.	1.3	V

V_{GD}

V V

DRM

3.

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FIG.1: Maximum power dissipation versus RMS on-state current

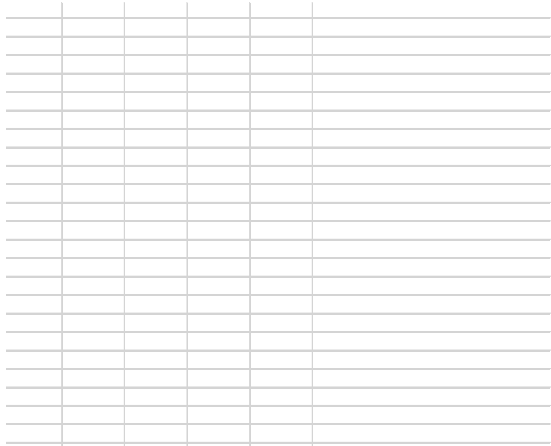


FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

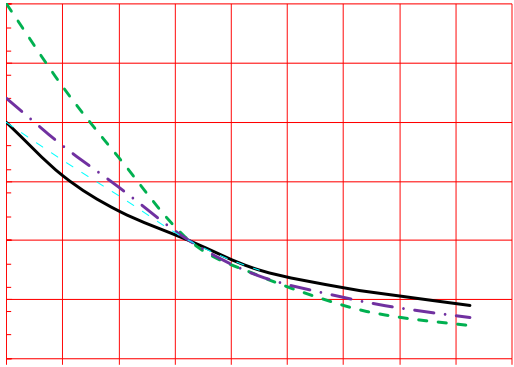


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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